

# **SB10W05P**

Schottky Barrier Diode (Twin Type - Cathode Common)

# 50V, 1A Rectifier

## **Applications**

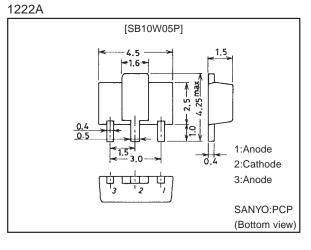
• High frequency rectification (switching regulators, converters, choppers).

## **Features**

- · Low forward voltage (V<sub>F</sub> max=0.55V).
- $\cdot$  Fast reverse recovery time (trr max=10ns).
- · Low switching noise.
- Low leakage current and high reliability due to highly reliable planar structure.

## **Package Dimensions**

unit:mm



# **Specifications**

#### Absolute Maximum Ratings at Ta = 25°C (Value per element)

Parameter	Symbol	Conditions	Ratings	Unit
Repetitive Peak Reverse Voltage	VRRM		50	V
Nonrepetitive Peak Reverse Surge Voltage	VRSM		55	V
Average Output Current	I <sub>O</sub>		1	A
Surge Forward Current	IFSM	50Hz sine wave, 1 cycle	10	A
Junction Temperature	Tj		-55 to +125	°C
Storage Temperature	Tstg		-55 to +125	°C

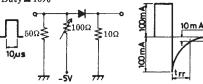
#### Electrical Characteristics at Ta = 25°C (Value per element)

Parameter	Symbol	Conditons	Ratings			Unit
			min	typ	max	
Reverse Voltage	VR	I <sub>R</sub> =300μA	50			V
Forward Voltage	٧ <sub>F</sub>	I <sub>F</sub> =1A			0.55	V
Reverse Current	IR	V <sub>R</sub> =25V			80	μA
Interterminal Capacitance	С	V <sub>R</sub> =10V, f=1MHz		52		pF
Reverse Recovery Time	trr	IF=IR=100mA, See specified Test Circuit.			10	ns
Thermal Resistance	Rth(j-a) (1)			280		°C/W
	Rth(j-c) (2)	Mounted on 250mm <sup>2</sup> ×0.8mm ceramic board		100		°C/W

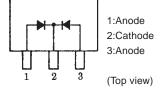
#### · Marking:SL

#### trr Test Circuit

Duty≤10%



### **Electrical Connection**



SANYO Electric Co., Ltd. Semiconductor Bussiness Headquaters TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110-8534 JAPAN 43098HA (KT)/53196GI/42294YH (KOTO) 8-7182 No.4170-1/2

### **SB10W05P**

